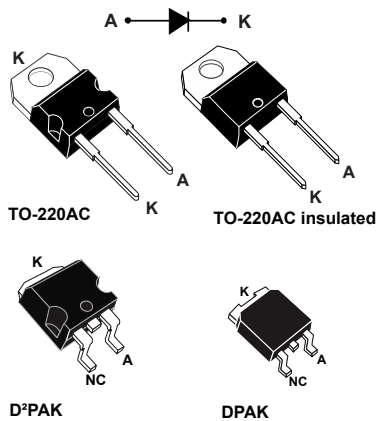


## 650 V, 6 A high surge silicon carbide power Schottky diode



### Features

- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- High forward surge capability
- Insulated package TO-220AC Ins:
  - Insulated voltage: 2500 V<sub>RMS</sub>
  - Typical package capacitance: 7 pF
- Power efficient product

### Applications

- Switch mode power supply
- PFC
- DCDC converters
- LLC topologies
- Boost diode

### Description

This 6 A, 650 V SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

This [STPSC6H065](#) is especially suited for use in PFC applications. This ST SiC diode will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

#### Product status

[STPSC6H065](#)

#### Product summary

Symbol	Value
I <sub>F(AV)</sub>	6 A
V <sub>RRM</sub>	650 V
T <sub>j(max.)</sub>	175 °C

#### Product label



# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)**

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	TO-220AC, DPAK, D <sup>2</sup> PAK, $T_c = 135\text{ °C}^{(1)}$ , DC	6	A
		TO-220AC Ins, $T_c = 110\text{ °C}^{(1)}$		
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal, $T_c = 25\text{ °C}$	60	A
		$t_p = 10\text{ ms}$ sinusoidal, $T_c = 125\text{ °C}$	52	
		$t_p = 10\text{ }\mu\text{s}$ square, $T_c = 25\text{ °C}$	400	
$I_{FRM}$	Repetitive peak forward current	TO-220AC, DPAK, D <sup>2</sup> PAK, $T_c = 135\text{ °C}^{(1)}$ , $T_j = 175\text{ °C}$ , $\delta = 0.1$	25	A
		TO-220AC Ins, $T_c = 95\text{ °C}$		
$T_{stg}$	Storage temperature range		-55 to +175	°C
$T_j$	Operating junction temperature range <sup>(2)</sup>		-40 to +175	°C

1. Value based on  $R_{th(j-c)}$  max.

2.  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

**Table 2. Thermal resistance parameters**

Symbol	Parameter		Typ. value	Max. value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC, DPAK, D <sup>2</sup> PAK	1.6	2.4	°C/W
		TO-220AC Ins	2.9	4.2	

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	5	60	$\mu\text{A}$
		$T_j = 150\text{ °C}$		-	50	250	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 6\text{ A}$	-	1.56	1.75	V
		$T_j = 150\text{ °C}$		-	1.98	2.50	

1.  $t_p = 10\text{ ms}$ ,  $\delta < 2\%$

2.  $t_p = 500\text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.192 \times I_{F(RMS)}^2$$

For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

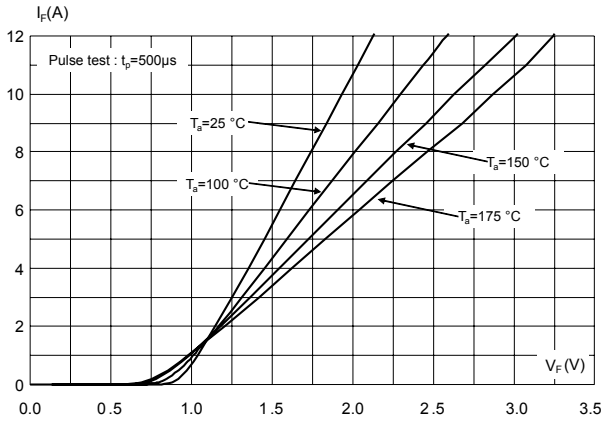
**Table 4. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{cj}^{(1)}$	Total capacitive charge	$V_R = 400 \text{ V}$	18	nC
$C_j$	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	300	pF
		$V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	30	

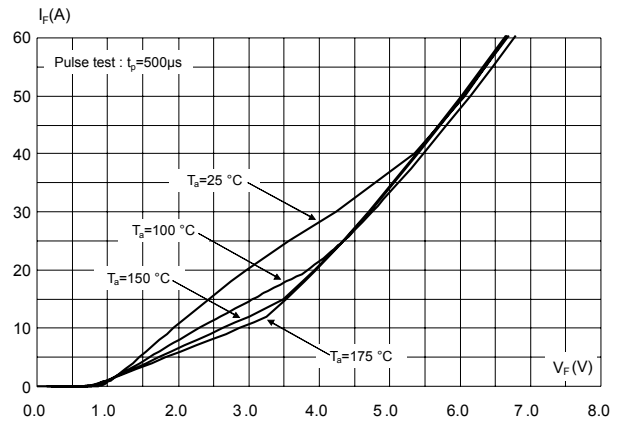
1. Most accurate value for the capacitive charge:  $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$

## 1.1 Characteristics (curves)

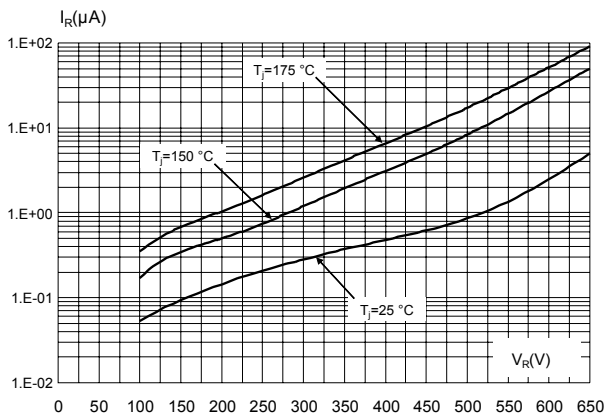
**Figure 1. Forward voltage drop versus forward current (typical values, low level)**



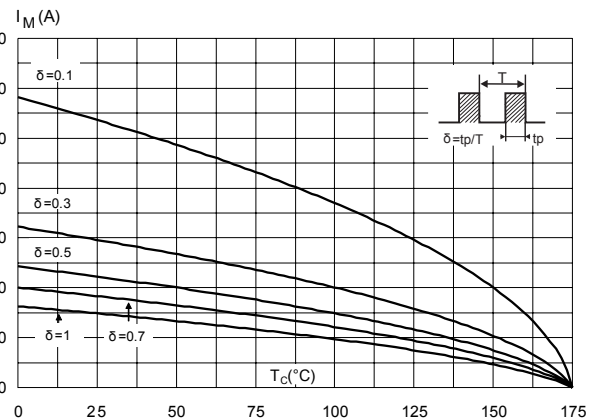
**Figure 2. Forward voltage drop versus forward current (typical values, high level)**



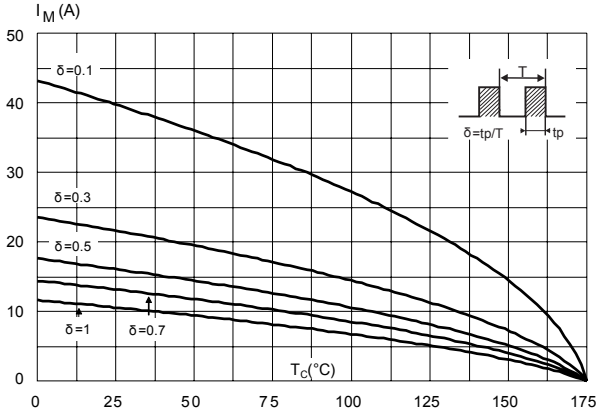
**Figure 3. Reverse leakage current versus reverse voltage applied (typical values)**



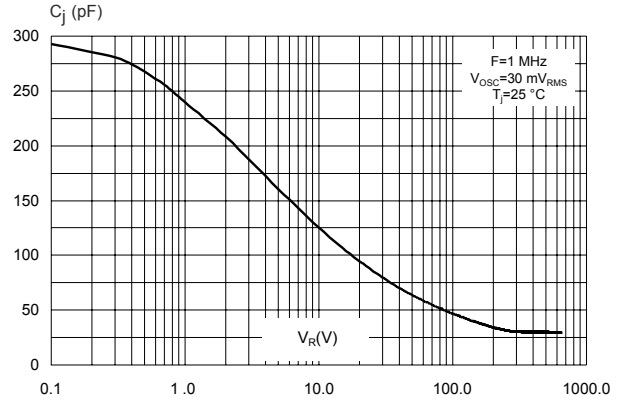
**Figure 4. Peak forward current versus case temperature (TO-220AC, DPAK, D<sup>2</sup>PAK)**



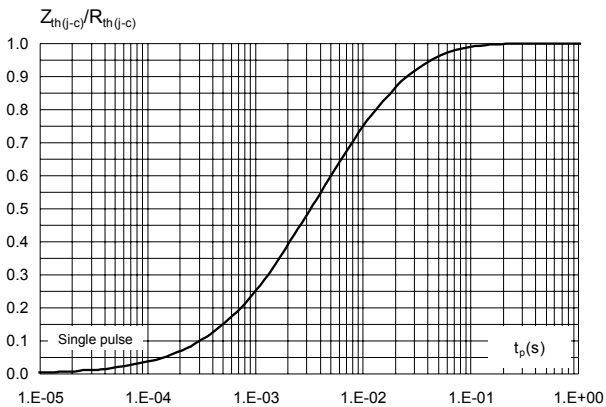
**Figure 5. Peak forward current versus case temperature (TO-220AC Ins)**



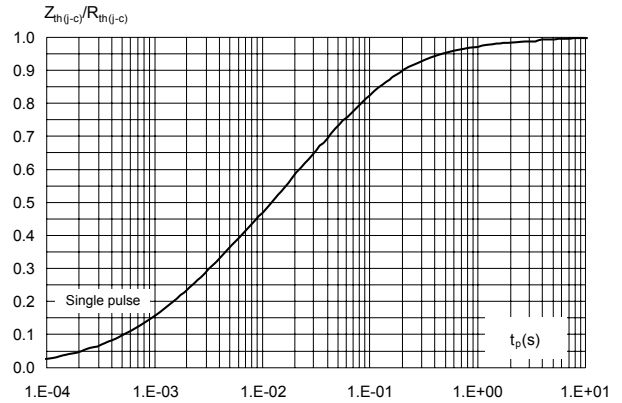
**Figure 6. Junction capacitance versus reverse voltage applied (typical values)**



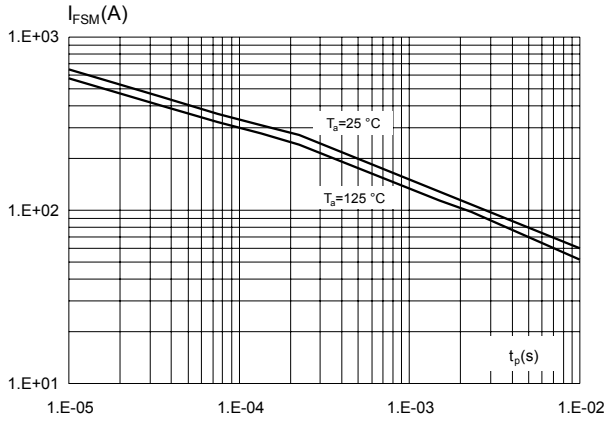
**Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC, DPAK and D<sup>2</sup>PAK)**



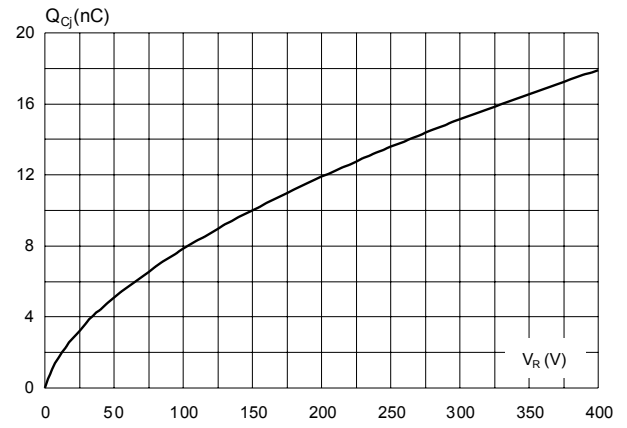
**Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC Ins)**



**Figure 9. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 10. Total capacitive charges versus reverse voltage applied (typical values)**



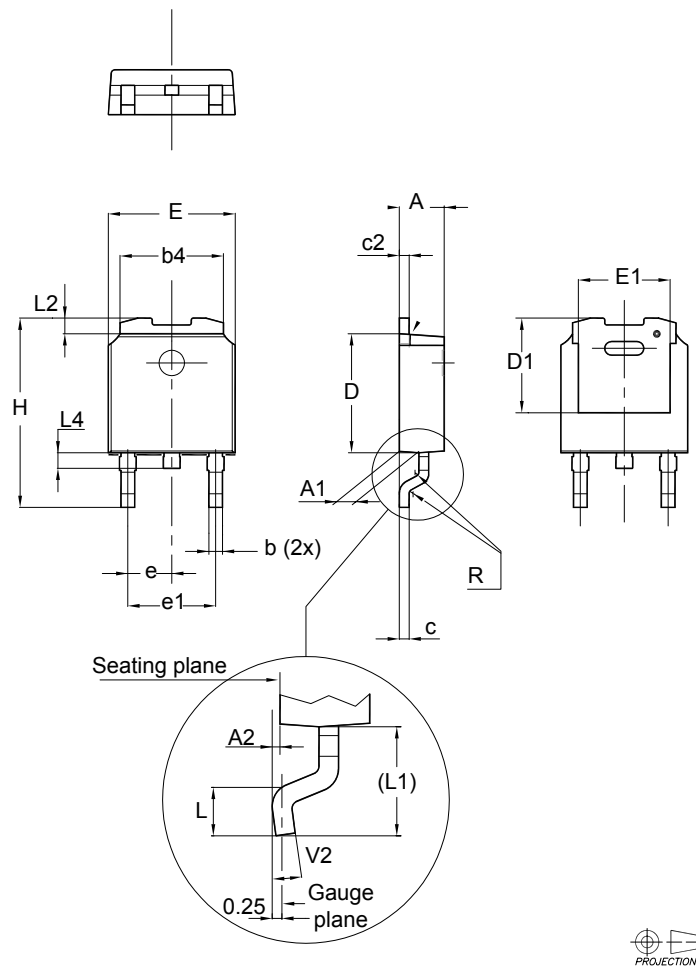
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 2.1 DPAK package information

- Epoxy meets UL94, V0
- Lead-free packages

**Figure 11. DPAK package outline**

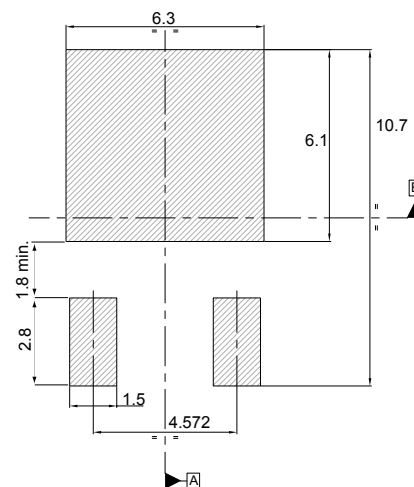


**Table 5. DPAK mechanical data**

Dim.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	5.20		5.40	0.205		0.213
c	0.45		0.60	0.018		0.024
c2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
D1	4.95	5.10	5.25	0.195	0.201	0.207
E	6.40		6.60	0.252		0.260
E1	4.60	4.70	4.80	0.181	0.185	0.189
e	2.159	2.286	2.413	0.085	0.090	0.095
e1	4.445	4.572	4.699	0.175	0.180	0.185
H	9.35		10.10	0.368		0.398
L	1.00		1.50	0.039		0.059
(L1)	2.60	2.80	3.00	0.102	0.110	0.118
L2	0.65	0.80	0.95	0.026	0.031	0.037
L4	0.60		1.00	0.024		0.039
R		0.20			0.008	
V2	0°		8°	0°		8°

1. Inches dimensions given for reference only

**Figure 12. DPAK recommended footprint (dimensions are in mm)**



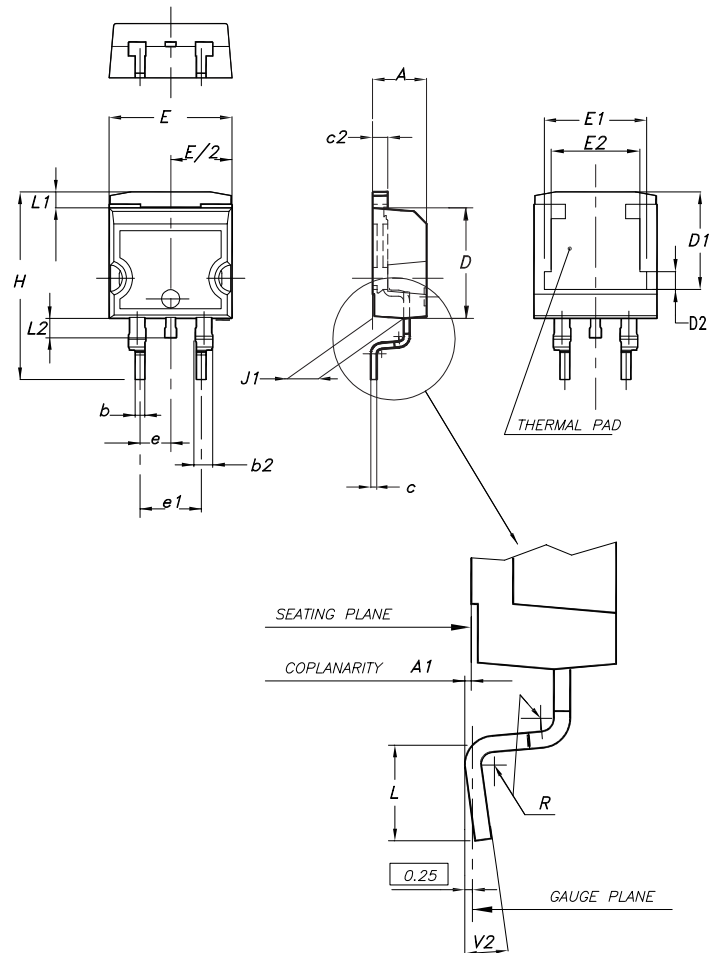
The device must be positioned within  $\Phi 0.05 \text{ A B}$



## 2.2 D<sup>2</sup>PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 13. D<sup>2</sup>PAK package outline

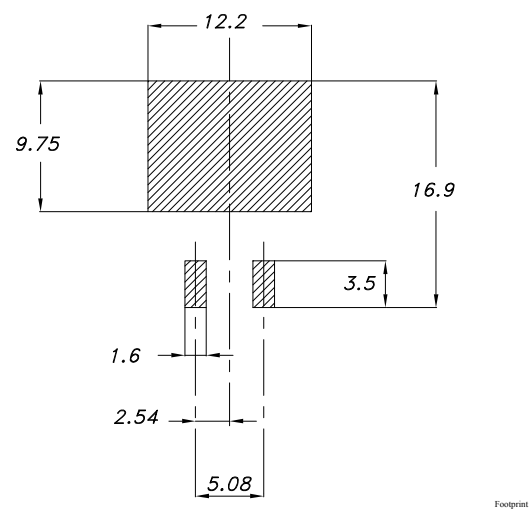


**Note:** This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. D<sup>2</sup>PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10.00		10.40	0.394		0.409
E1	8.30	8.50	8.70	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15.00		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.40			0.015	
V2	0°		8°	0°		8°

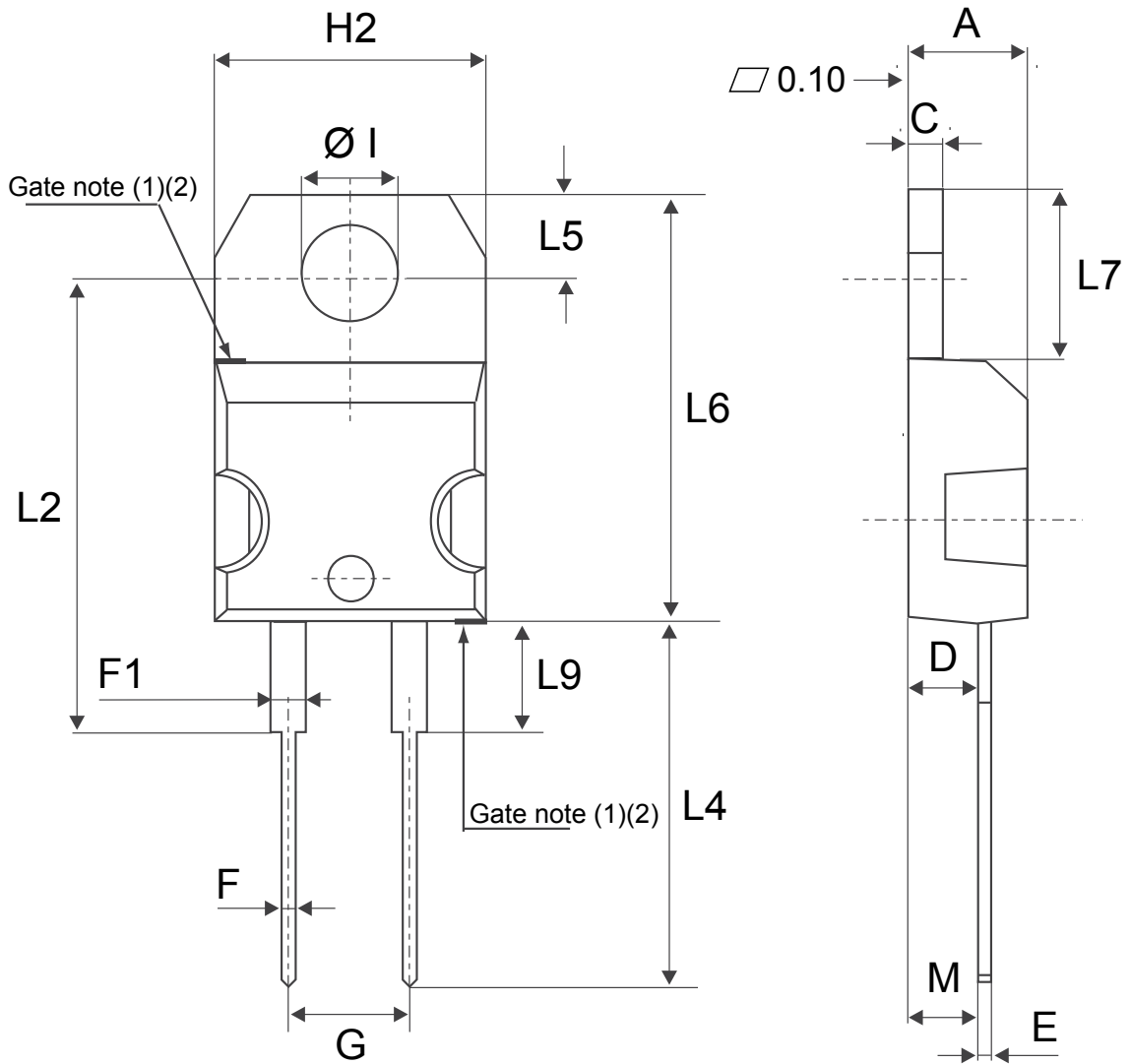
Figure 14. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)



### 2.3 TO-220AC package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 15. TO-220AC package outline



(1) :Max resin gate protusion 0.5 mm

(2) :Resin gate position is accepted in each of the two positions shown on the drawings or their symmetrical

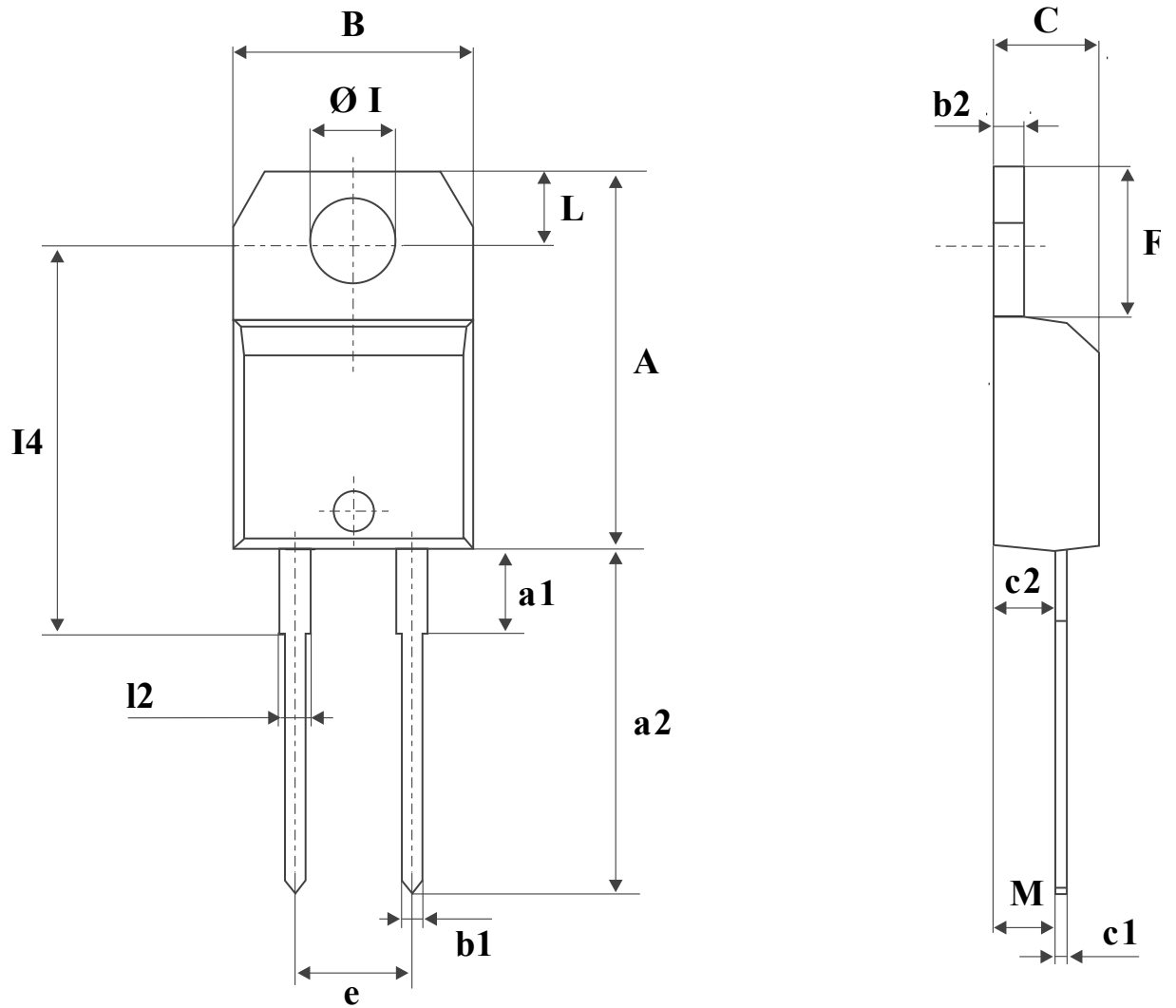
**Table 7. TO-220AC package mechanical data**

Ref.	Dimensions			
	Millimeters		Inches (for reference only)	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.60 typ.		0.102 typ.	
Diam	3.75	3.85	0.147	0.151

## 2.4 TO-220AC Ins package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 16. TO-220AC Ins package outline



**Table 8. TO-220AC Ins package mechanical data**

Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	4.80		5.40	0.189		0.212
F	6.20		6.60	0.244		0.259
L	2.65		2.95	0.104		0.116
l2	1.14		1.70	0.044		0.066
l4	15.80	16.40	16.80	0.622	0.645	0.661
M		2.60			0.102	
Øl	3.75		3.85	0.147		0.151

### 3 Ordering Information

**Table 9. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC6H065D	STPSC6H065D	TO-220AC	1.86 g	50	Tube
STPSC6H065DI	STPSC 6H065DI	TO-220AC Ins	2.12 g	50	Tube
STPSC6H065G-TR	STPSC6H065G	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel
STPSC6H065B-TR	STPSC 6H065	DPAK	0.32 g	2500	Tape and reel

## Revision history

**Table 10. Document revision history**

Date	Version	Changes
18-Jun-2012	1	First issue.
31-Aug-2012	2	Added diode configuration graphic on front page. Updated value of $Q_{cj}$ and footnote equation in Table 5.
10-Oct-2012	3	Added Max. value in Table 3.
07-Nov-2013	4	Updated Figure 1, Figure 2, Figure 13, Figure 14, and Table 9.
07-Jan-2014	5	Added TO-220AC Ins package.
22-Jul-2015	6	Updated Table 10 and reformatted to current standard.
22-Feb-2016	7	Updated cover image.
25-Jan-2019	8	Updated D <sup>2</sup> PAK package information. Added <a href="#">Section Applications</a> and <a href="#">Section Sustainable technology program</a> .



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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

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